



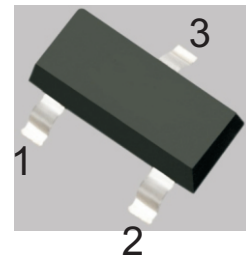
BC856 BC857 BC858

PNP TRANSISTOR

FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

SOT-23



1.BASE  
2.EMITTER  
3.COLLECTOR

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

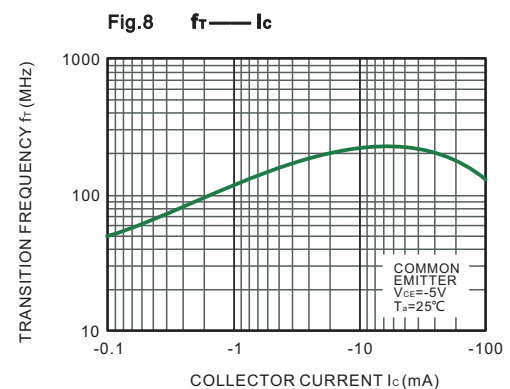
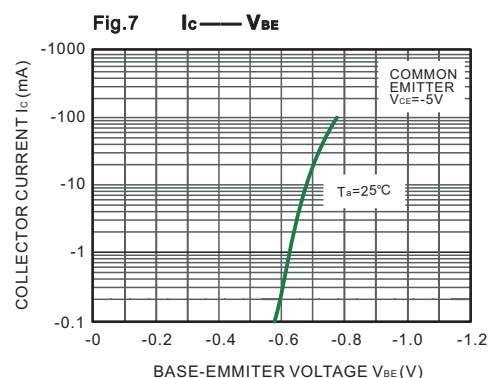
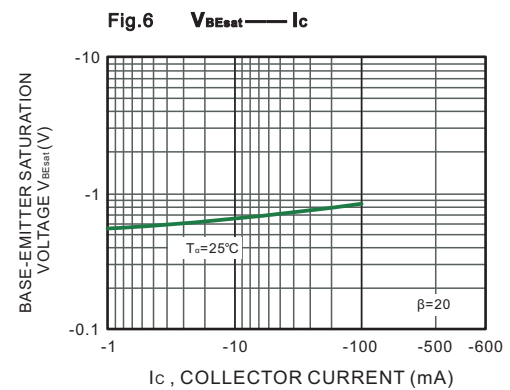
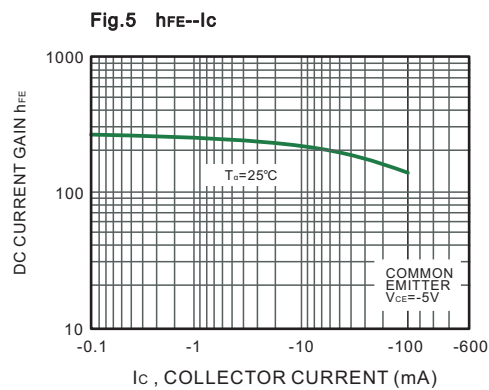
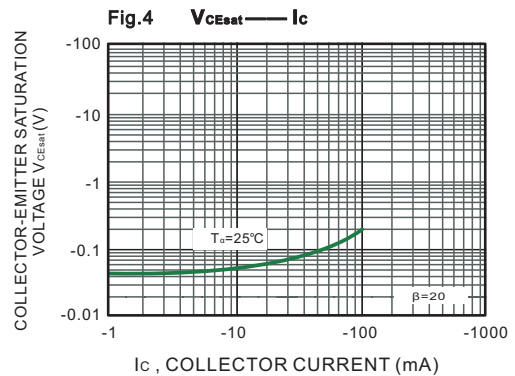
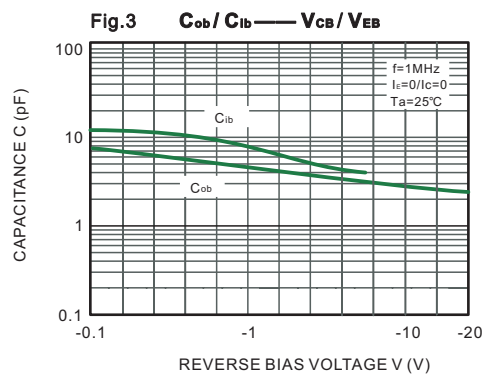
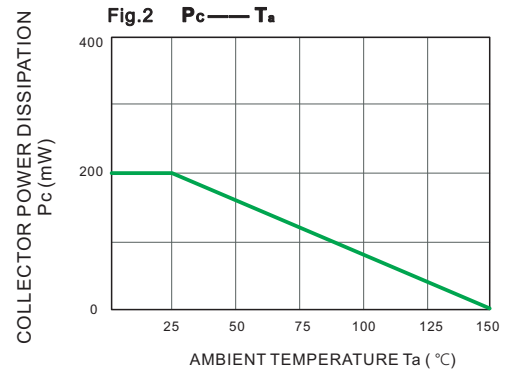
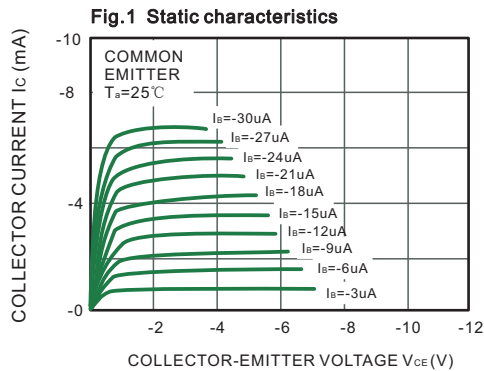
Parameter	Symbol	Value	Unit
Collector–Base Voltage	V <sub>CBO</sub>	BC856 -80	V
		BC857 -50	
		BC858 -30	
Collector–Emitter Voltage	V <sub>CEO</sub>	BC856 -65	V
		BC857 -45	
		BC858 -30	
Emitter–Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current — Continuous	I <sub>C</sub>	-0.1	A
Collector Power Dissipation	P <sub>C</sub>	200	mW
Thermal Resistance From Junction To Ambient	R <sub>thJA</sub>	625	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-65~+150	°C

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V <sub>CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> = 0	BC856 -80		V
			BC857 -50		
			BC858 -30		
Collector-emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> = 0	BC856 -65		V
			BC857 -45		
			BC858 -30		
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -1μA, I <sub>C</sub> = 0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -70V, I <sub>E</sub> = 0 V <sub>CB</sub> = -45V, I <sub>E</sub> = 0 V <sub>CB</sub> = -25V, I <sub>E</sub> = 0	BC856 -0.1		μA
			BC857		
			BC858		
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> = -60V, I <sub>B</sub> = 0 V <sub>CE</sub> = -40V, I <sub>B</sub> = 0 V <sub>CE</sub> = -25V, I <sub>B</sub> = 0	BC856 -0.1		μA
			BC857		
			BC858		
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> = 0	-0.1		μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -2mA	BC856A, 857A, 858A 125	250	
			BC856B, 857B, 858B 220		
			BC857C, BC858C 420		
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA	-0.5		V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA	-1.1		V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA, f = 100MHz	100		MHz
Collector capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, f = 1MHz	4.5		pF

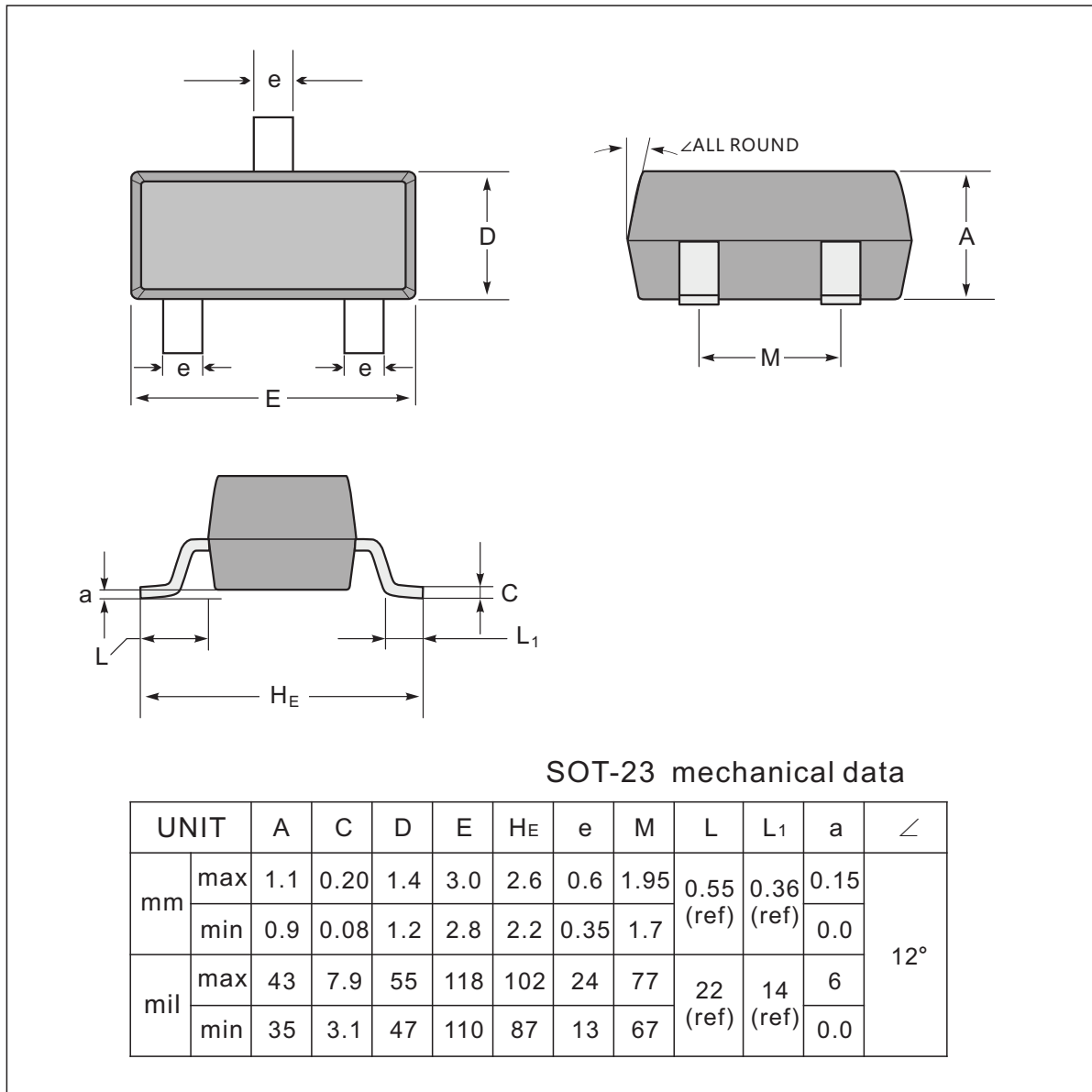


### TYPICAL CHARACTERISTICS

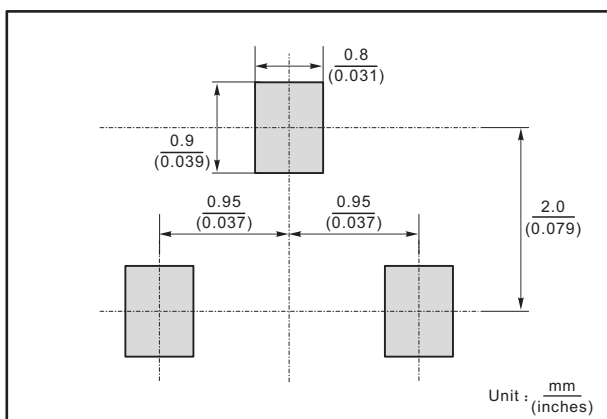




### SOT-23 Package Outline Dimensions



#### The recommended mounting pad size



#### Marking

Type number	Marking code
BC856A	3A
BC856B	3B
BC857A	3E
BC857B	3F
BC857C	3G
BC858A	3J
BC858B	3K
BC858C	3L

单击下面可查看定价，库存，交付和生命周期等信息

[>>JINGDAO\(晶导微\)](#)